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	Application No.	Applicant(s)	
Notice of Allowshillty	10/648,482	JOEI, MASAHIRO	·
Notice of Allowability	Examiner	Art Unit	
	Lynne A. Gurley	2812	
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS therewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	(OR REMAINS) CLOSED in this ap or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due co	f ourse. THIS
1. 🔀 This communication is responsive to the interview summar	y of 4/28/04 and Attorney's approva	<u>l given 5/10/04</u> .	
2. ⊠ The allowed claim(s) is/are <u>1-10</u> .			
3. $igotimes$ The drawings filed on <u>27 August 2003</u> are accepted by the	Examiner.		
4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submained in the Notice of Draftspers (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the paper No. INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT (see 2. Comment regarding REQUIREMENT).	been received. been received in Application No cuments have been received in this of this communication to file a reply ENT of this application. itted. Note the attached EXAMINER as reason(s) why the oath or declara at be submitted. on's Patent Drawing Review (PTO- as Amendment / Comment or in the Comment of the drawing the header according to 37 CFR 1.121(sit of BIOLOGICAL MATERIAL I	national stage application of the following with the requestion is deficient. 948) attached office action of the following in the front (not the following).	DTICE OF
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛭 Examiner's Statemer 9. 🗍 Other	(PTO-413), te <u>5/10/04</u> . ment/Comment	vance
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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Ramyar M. Farid on 5/10/04.

The application has been amended as follows:

In the Claims:

1. (Currently amended) A method for fabricating a semiconductor device comprising the steps of:

forming an insulating film on a conductive pattern formed on a substrate; forming a resist pattern on the insulating film;

performing etching to the insulating film using the resist pattern as a mask to form in the insulating film an opening at which part of a surface of the conductive pattern is exposed;

forming, by performing oxygen plasma treatment, a passive antioxidant layer on the part of the surface of the conductive pattern exposed while removing the resist pattern; and

depositing a conductive film on the conductive pattern from which the antioxidant layer has been removed,

wherein the antioxidant layer contains CuO as a main component.

- 2. (Currently amended) The method of claim 1, wherein the conductive pattern contains Cu and the antioxidant layer contains CuO as a main component.
- 3. (Previously presented) The method of claim 2, wherein the step of forming an antioxidant layer includes performing oxygen plasma treatment with a substrate temperature of 120°C or less.
- 4. (Original) The method of claim 2, wherein the step of forming an antioxidant layer includes performing oxygen plasma treatment with a chamber pressure of 40 Pa or less.

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5. (Currently amended) A method for fabricating a semiconductor device comprising the steps

of:

forming an insulating film on a conductive pattern formed on a substrate;

forming a resist pattern on the insulating film;

performing etching to the insulating film using the resist pattern as a mask to form in the insulating film an opening at which part of the surface of the conductive pattern is exposed;

forming, by performing oxygen plasma treatment, a passive antioxidant layer on the part of the surface of the conductive pattern exposed;

after forming the antioxidant layer, removing the resist pattern by performing oxygen plasma treatment; and

depositing a conductive film on the conductive pattern from which the antioxidant layer has been removed,

wherein the antioxidant layer contains CuO as a main component.

- 6. (Currently amended) The method of claim 5, wherein the conductive pattern contains Cu and the antioxidant layer contains CuO as a main component.
- 7. (Previously presented) The method of claim 6, wherein the step of removing the resist pattern includes performing oxygen plasma treatment with a substrate temperature of not less than 200°C and not more than 250°C.

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8. (Original) The method of claim 5, wherein the step of forming an antioxidant layer includes performing oxygen plasma treatment with a first substrate temperature, and

the step of removing the resist pattern includes performing oxygen plasma treatment with a second substrate temperature which is higher than the first substrate temperature.

9. (Original) The method of claim 5, wherein the step of forming an antioxidant layer includes performing oxygen plasma treatment at a first pressure, and

the step of removing the resist pattern includes performing oxygen plasma treatment at a second pressure which is higher than the first pressure.

10. (Previously presented) The method of claim 5, wherein the step of forming the antioxidant layer includes performing reactive ion treatment to the conductive pattern.

Reasons For Allowance

2. The following is an examiner's statement of reasons for allowance: The closest prior art of record fails to teach or to suggest, that "the antioxidant layer contains CuO as a main component".

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynne A. Gurley whose telephone number is 571-272-1670. The examiner can normally be reached on M-F 7:30-4:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on 571-272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Lynne A. Gurley

Primary Patent Examiner

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TC 2800, AU 2812

LAG May 10, 2004